## Silicon Switching Diode

1N4608

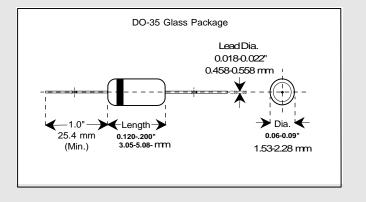
## **DO-35 Glass Package**

## **Applications**

Used in general purpose applications, where a controlled forward characteristic and fast switching speed are important.

## Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond<sup>™</sup> plating for problem free solderability



Maximum Ratings			Symbo	I Value	Unit
Peak Inverse Voltage			PIV	85 (Min).	Volts
Average Rectified Current			lavg	200	mAmps
Continuous Forward Current			l Fdc	500	mAmps
Peak Surge Current (t <sub>peak</sub> = 1 sec.)			l <sub>peak</sub>	1.0	Amp
BKC Power Dissipation $T_L=50 \circ C$ , L = 3/8" from body			P <sub>tot</sub>	500	mWatts
Operating Temperature Range			T <sub>Op</sub>	-65 to +150	° C
Storage Temperature Range			T <sub>st</sub>	-65 to +150	° C
Electrical Characteristics @ 25 °C*	Symbol	Mi	nimum	Maximum	Unit
Forward Voltage Drop @ $I_F = 400 \text{ mA}$	$V_{F}$	*	**	1.10	Volts
Breakdown Voltage @  I <sub>R</sub> =25 µA	PIV	٤	35		Volts
Reverse Leakage Current @ V <sub>R</sub> = 50 V	l <sub>R</sub>			100	μA
Reverse Recovery time (note 1)	t <sub>rr</sub>			10	nSecs

Note 1: Per Method 4031-A with I<sub>F</sub> = 10 mA, Vr = 6 V, R<sub>I</sub> = 100 Ohms. \* UNLESS OTHERWISE SPECIFIED

